

2 x 32W DUAL BRIDGE CAR RADIO AMPLIFIER

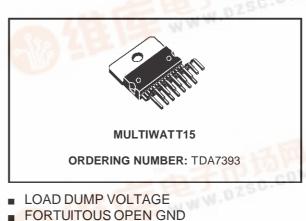
- HIGH OUTPUT POWER CAPABILITY: 2 x 35W max./4Ω 2 x 32W EIAJ/4 Ω 2 x 22W typ./4Ω @ 14.4V, 1KHz, 10% 2 x 19W typ./4Ω @ 13.2V, 1KHz, 10% 2 x 28W typ./2Ω @ 14.4V, 1KHz, 10%
- 2 x 25W typ./2Ω @ 13.2V, 1KHz, 10%
- LOW DISTORTION
- LOW OUTPUT NOISE
- ST-BY FUNCTION
- MUTE FUNCTION
- AUTO-MUTE AT MIN. SUPPLY VOLTAGE DETECTION
- LOW EXTERNAL COMPONENT COUNT - INTERNALLY FIXED GAIN (32dB)
 - NO EXTERNAL COMPENSATION
 - NO BOOTSTRAP CAPACITORS
- ADDITIONAL MONO INPUT A DAL

PROTECTIONS:

- OUTPUT AC/DC SHORT CIRCUIT TO GND AND TO Vs
- VERY INDUCTIVE LOADS
- OVERRATING CHIP TEMPERATURE WITH SOFT THERMAL LIMITER

BLOCK DIAGRAM

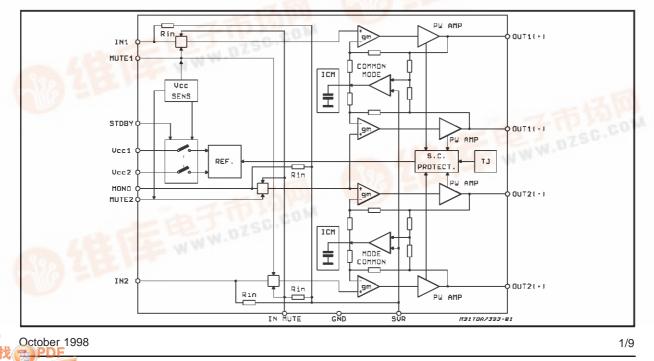
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- **REVERSE BATTERY**
- ESD PROTECTION

DESCRIPTION

The TDA7393 is a new technology class AB Audio Power Amplifier in Multiwatt15 package designed for high end car radio applications. Thanks to the fully complementary PNP/NPN output configuration the high power performances of the TDA7393 are obtained without bootstrap capacitors. The extremely reduced components count

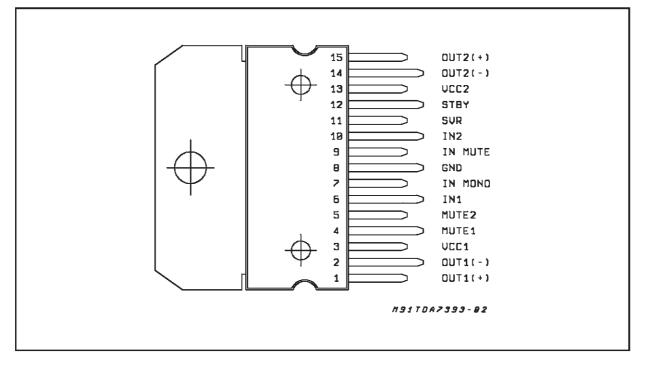


ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Operating Supply Voltage	18	V
V _{CC (DC)}	DC Supply Voltage	28	V
V _{CC (pk)}	Peak Supply Voltage (t = 50ms)	50	V
Ι _Ο	Output Peak Current: Repetitive (Duty Cycle 10% at $f = 10Hz$) Non Repetitive ($t = 100\mu s$)	4.5 5.5	A
P _{tot}	Power dissipation, Tcase = 75°C (see derating curve)	50	W
Тi	Junction Temperature	150	°C
T _{op}	Operating Ambient Temperature	– 40 to 85	°C
T _{stg}	Storage Temperature	- 55 to 150	°C

allows very compact sets.

PIN CONNECTION (Top view)



THERMAL DATA

Symbol	Parameter	Value	Unit	
R _{th j-case}	Thermal Resistance Junction to Case	Max.	1.5	°C/W

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
I _{q1}	Quiescent Current			90	180	mA
Vos	Output Offset Voltage				150	mV
Gv	Voltage Gain		30.5	32	33.5	dB
Po	Output Power	$\begin{array}{l} THD = 10\%; V_S = 14.4V \\ THD = 10\% \\ THD = 1\% \\ THD = 10\%; R_L = 2\Omega \\ THD = 10\%; V_S = 14.4V; \\ R_L = 2\Omega \end{array}$	17	22 19 16 25 28		W W W W
P _{o max}	Max. Output Power	EIAJ RULES; V _S = 13.7V		30		w
THD	Distortion	$P_0 = 0.1$ to 8W		0.08	0.3	%
e _{No}	Output Noise	Bw = 20Hz to 20KHz			0.3	mVrms
SVR	Supply Voltage Rejection	f = 100Hz (stereo)		60		dB
f∟	Low Cut-Off Frequency			10		Hz
fн	High Cut-Off Frequency			300		KHz
Ri	Input Impedance		10	15	20	KΩ
CT	Cross Talk	f = 1KHz	50	65		dB
I _{SB}	St-By Current Consumption				100	μΑ
V _{SB out}	St-By OUT Threshold Voltage	Amp. ON	3.5			V
V _{SB IN}	St-By IN Threshold Voltage	Amp. OFF			1.5	V
V _{SB}	Supply Dependent St-By Threshold	St-By = H, V _S reducing/increasing		7.5	8.3	V
A _M	Mute Attenuation	V _O = 1Vrms		75		dB
V _{M out}	Mute OUT Threshold Voltage	Amp. Play	3.5			V
V _{M in}	Mute IN Threshold Voltage	Amp. Mute			1.5	V
V _M	Supply Dependent Mute Threshold	Mute = IN, V _S reducing/increasing		8.5	9.3	V
I _{m (L)}	Muting Pin Current	V _{MUTE} = 1.5V (Sourced Current)	6	10	14	μΑ
I _{m (H)}	Muting Pin Current	VMUTE = 3.5V (Sourced Current)	6	10	14	μΑ

ELECTRICAL CHARACTERISTICS (V_S = 13.2V; f = 1KHz; R_g = 600Ω ; R_L = 4Ω ; T_{amb} = 25° C; Refer to the application circuit, unless otherwise specified.)



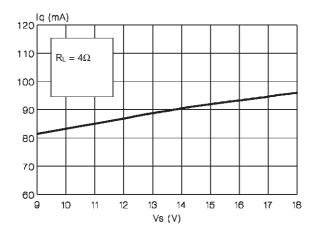
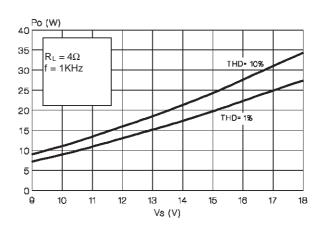


Figure 2: Output Power vs. Supply Voltage





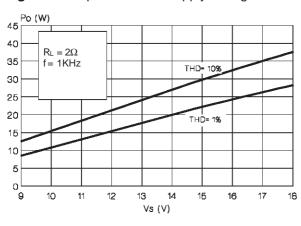
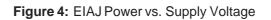


Figure 3: Output Power vs Supply Voltage



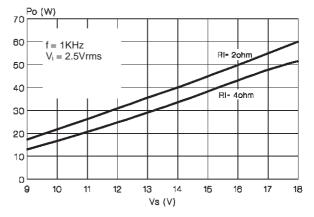


Figure 5: Cross-Talk vs. Frequency

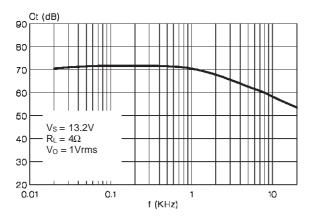


Figure 7: Distortion vs. Frequency

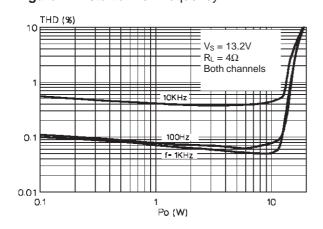


Figure 6: SVR vs. Frequency

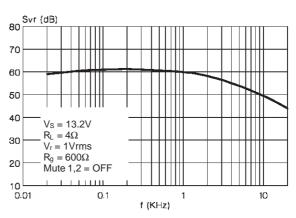
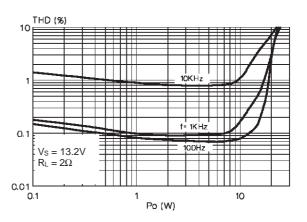


Figure 8: Distortion vs. Frequency



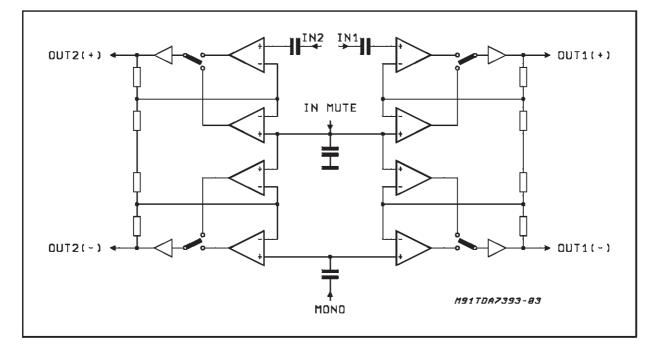


Figure 9: Block Diagram of Mute Circuit

Figure 10: Explanatory Waveforms Of Mute Circuit

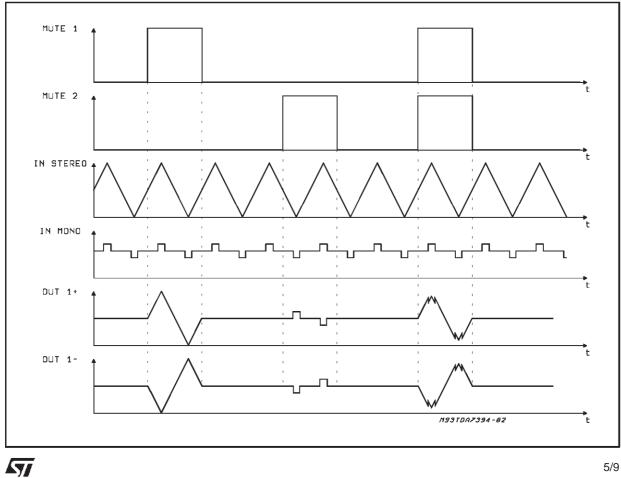


Figure 11: Application Circuit

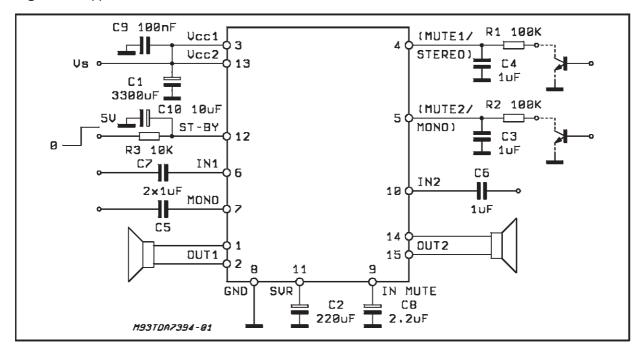
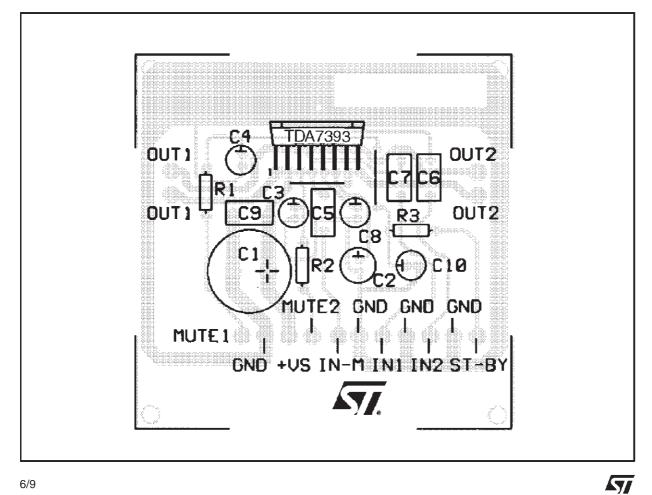


Figure 12: P.C. Board and Component Layout of the fig. 11 (1:1 scale)



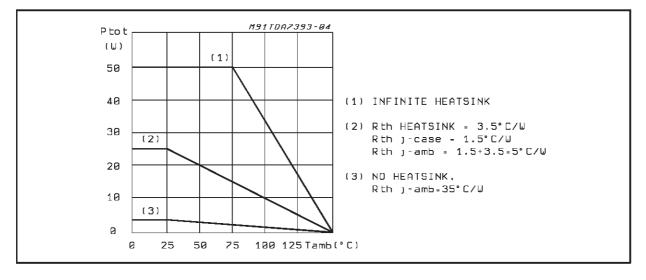
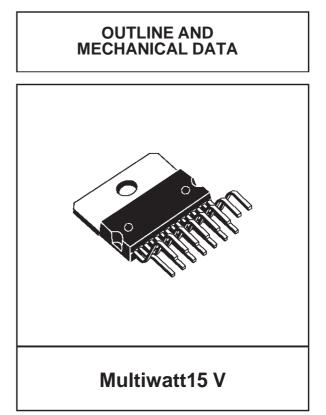
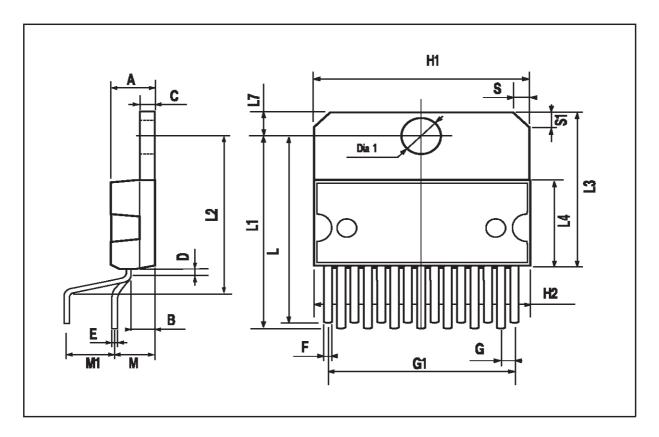


Figure 13: Power Dissipation Derating Curve

DIM.	mm			inch			
Dilvi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А			5			0.197	
В			2.65			0.104	
С			1.6			0.063	
D		1			0.039		
Е	0.49		0.55	0.019		0.022	
F	0.66		0.75	0.026		0.030	
G	1.02	1.27	1.52	0.040	0.050	0.060	
G1	17.53	17.78	18.03	0.690	0.700	0.710	
H1	19.6			0.772			
H2			20.2			0.795	
L	21.9	22.2	22.5	0.862	0.874	0.886	
L1	21.7	22.1	22.5	0.854	0.870	0.886	
L2	17.65		18.1	0.695		0.713	
L3	17.25	17.5	17.75	0.679	0.689	0.699	
L4	10.3	10.7	10.9	0.406	0.421	0.429	
L7	2.65		2.9	0.104		0.114	
М	4.25	4.55	4.85	0.167	0.179	0.191	
M1	4.63	5.08	5.53	0.182	0.200	0.218	
S	1.9		2.6	0.075		0.102	
S1	1.9		2.6	0.075		0.102	
Dia1	3.65		3.85	0.144		0.152	

MULTIWATT15 PACKAGE MECHANICAL DATA





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